

## TH58BYG2S3HBAI6

#### TH58BYG2S3HBAI6 Information



For Reference Only

Part Number TH58BYG2S3HBAI6

Manufacturer Toshiba Semiconductor and Storage

Category Integrated Circuits (ICs)

Memory

**Description** IC EEPROM 4GBIT 25NS 67FBGA

Package 67-VFBGA

For the pricing/inventory/lead time, please contact

us

Website: https://www.heisener.com E-mail: salesdept@heisener.com



Request a Quote

# **Certified Quality**

Heisener's commitment to quality has shaped our processes for sourcing, testing, shipping, and every step in between. This foundation underlies each component we sell.









## TH58BYG2S3HBAI6 Specifications

Operating Temperature	-40°C ~ 85°C (TA)
Voltage - Supply	1.7 V ~ 1.95 V
Access Time	25ns
Write Cycle Time - Word, Page	25ns
Clock Frequency	-
Memory Interface	Parallel
Memory Size	4Gb (512M x 8)
Technology	EEPROM - NAND
Memory Format	EEPROM
Memory Type	Non-Volatile
Series	Benand?
Package	67-VFBGA
Category	Memory
Category	Toshiba Semiconductor and Storage Integrated Circuits (ICs)
Manufacturer Part Number  Manufacturer	TH58BYG2S3HBAI6

#### TH58BYG2S3HBAI6 Guarantees



#### **Quality Guarantees**

We provide 90 days warranty. \*

If the items you received were not in perfect quality, we would be responsible for your refund or replacement, but the items must be returned in their original condition.



#### **Service Guarantees**

We guarantee 100% customer satisfaction.

Our experienced sales team and tech support team back our services to satisfy all our customers.

### TH58BYG2S3HBAI6 Payment Methods



















### TH58BYG2S3HBAI6 Shipping Methods













If you have any question about TH58BYG2S3HBAI6, please do not hesitate to contact us!

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